

CSD13302W 12 V N Channel NexFET™ Power MOSFET

1 Features

- Ultra Low On Resistance
- Low Q_g and Q_{gd}
- Small Footprint 1 mm × 1 mm
- Low Profile 0.62 mm Height
- Pb Free
- RoHS Compliant
- Halogen Free

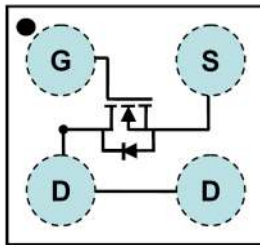
2 Applications

- Battery Management
- Load Switch
- Battery Protection

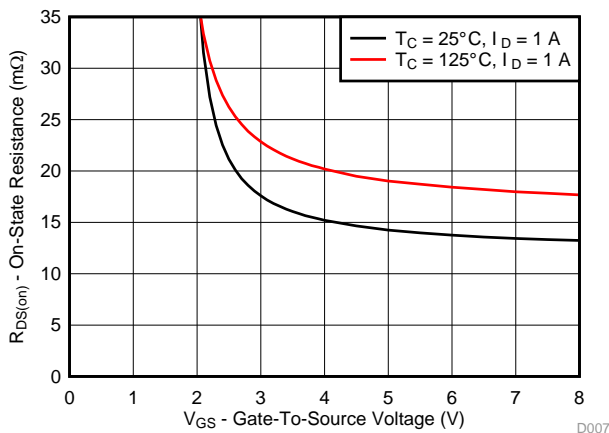
3 Description

This 14.6 mΩ, 12 V, N-Channel device is designed to deliver the lowest on resistance and gate charge in a small 1 x 1 mm outline with excellent thermal characteristics and an ultra low profile.

Top View

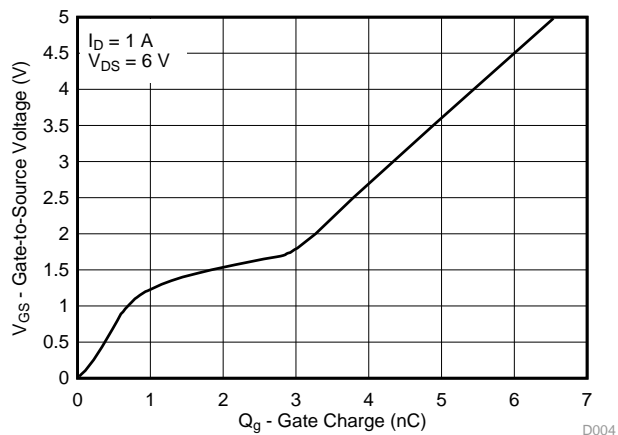


$R_{DS(on)}$ vs V_{GS}



D007

Gate Charge



D004

Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	12		V
Q_g	Gate Charge Total (4.5 V)	6.0		nC
Q_{gd}	Gate Charge Gate-to-Drain	2.1		nC
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 2.5\text{ V}$	21.2	mΩ
		$V_{GS} = 4.5\text{ V}$	14.6	mΩ
$V_{GS(th)}$	Threshold Voltage	1.0		V

Ordering Information⁽¹⁾

Device	Qty	Media	Package	Ship
CSD13302W	3000	7-Inch Reel	1.0 mm × 1.0 mm Wafer Level Package	Tape and Reel
CSD13302WT	250	7-Inch Reel		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	12	V
V_{GS}	Gate-to-Source Voltage	±10	V
I_D	Continuous Drain Current ⁽¹⁾	1.6	A
I_{DM}	Pulsed Drain Current ⁽²⁾	29	A
P_D	Power Dissipation ⁽³⁾	1.8	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C

(1) Device Operating at a temperature of 105°C

(2) Min Cu Typ $R_{\theta JA} = 275^\circ\text{C/W}$, Pulse width $\leq 100\ \mu\text{s}$, duty cycle $\leq 1\%$

(3) Max Cu Typ $R_{\theta JA} = 70^\circ\text{C/W}$



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4 Revision History

DATE	REVISION	NOTES
March 2015	*	Initial release.

5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^\circ\text{C})$

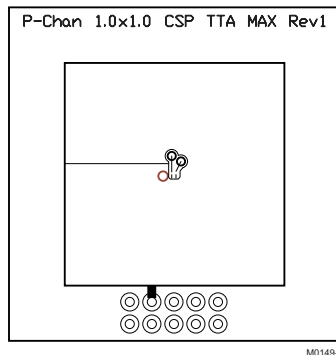
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
V_{DSS}	Drain-to-Source Voltage	$V_{GS} = 0, I_D = 250 \mu\text{A}$	12			V
I_{DSS}	Drain-to-Source Leakage Current	$V_{GS} = 0 \text{ V}, V_{DS} = 9.6 \text{ V}$			1	μA
I_{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0 \text{ V}, V_{GS} = 10 \text{ V}$			100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	0.7	1.0	1.3	V
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 2.5 \text{ V}, I_D = 1 \text{ A}$		21.2	25.8	m Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$		14.6	17.1	
g_{fs}	Transconductance	$V_{DS} = 1.2 \text{ V}, I_D = 1 \text{ A}$		10		S
DYNAMIC CHARACTERISTICS						
C_{ISS}	Input Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 6 \text{ V}, f = 1 \text{ MHz}$		663	862	pF
C_{OSS}	Output Capacitance			211	274	pF
C_{RSS}	Reverse Transfer Capacitance			151	196	pF
R_g	Series Gate Resistance	$V_{DS} = 6 \text{ V}, I_D = 1 \text{ A}$		3.6	7.2	Ω
Q_g	Gate Charge Total (4.5 V)			6.0	7.8	nC
Q_{gd}	Gate Charge Gate-to-Drain			2.1		nC
Q_{gs}	Gate Charge Gate-to-Source			0.7		nC
$Q_{g(th)}$	Gate Charge at V_{th}			0.7		nC
Q_{OSS}	Output Charge	$V_{DS} = 6 \text{ V}, V_{GS} = 0 \text{ V}$		1.3		nC
$t_{d(on)}$	Turn On Delay Time	$V_{DS} = 6 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$ $R_G = 0 \Omega$		6		ns
t_r	Rise Time			7		ns
$t_{d(off)}$	Turn Off Delay Time			17		ns
t_f	Fall Time			7		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	$I_S = 1 \text{ A}, V_{GS} = 0 \text{ V}$		0.7	1.0	V
Q_{rr}	Reverse Recovery Charge	$V_{DS} = 6 \text{ V}, I_S = 1 \text{ A}, di/dt = 200 \text{ A}/\mu\text{s}$		11.6		nC
t_{rr}	Reverse Recovery Time			19.6		ns

5.2 Thermal Information

 $(T_A = 25^\circ\text{C unless otherwise stated})$

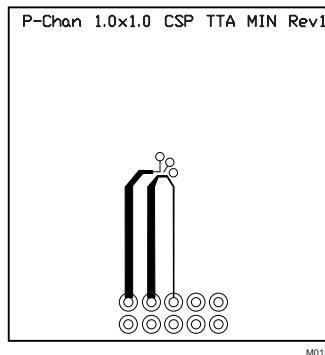
THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ⁽¹⁾		275		$^\circ\text{C}/\text{W}$
	Junction-to-Ambient Thermal Resistance ⁽²⁾		70		

(1) Device mounted on FR4 material with minimum Cu mounting area.

(2) Device mounted on FR4 material with 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu.


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Typical $R_{\theta JA} = 70^\circ\text{C}/\text{W}$
when mounted on
1 inch² of 2 oz. Cu.

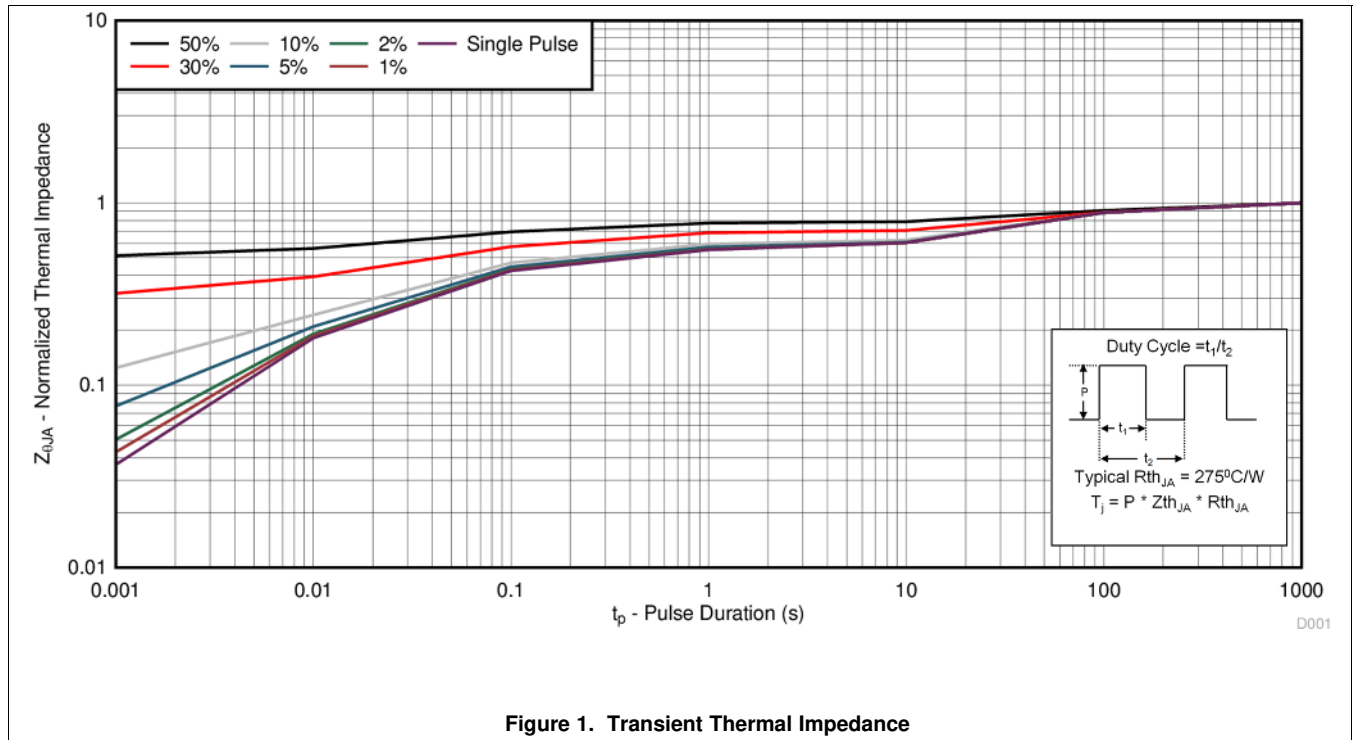


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Typical $R_{\theta JA} = 275^\circ\text{C}/\text{W}$
when
mounted on minimum
pad area of 2 oz. Cu.

5.3 Typical MOSFET Characteristics

($T_A = 25^\circ\text{C}$ unless otherwise stated)



Typical MOSFET Characteristics (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

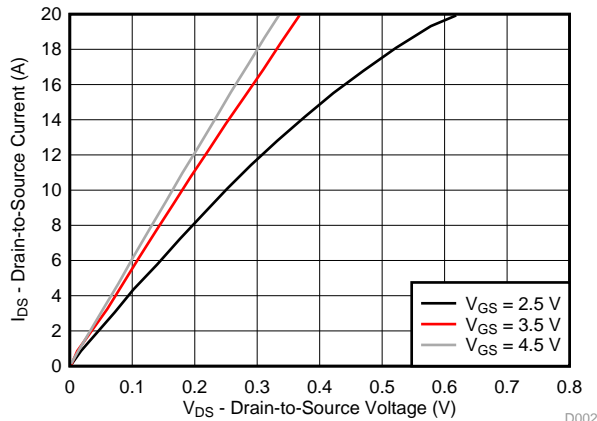


Figure 2. Saturation Characteristics

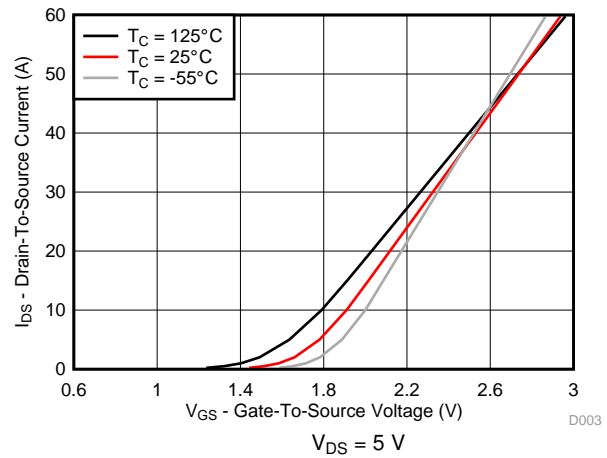


Figure 3. Transfer Characteristics

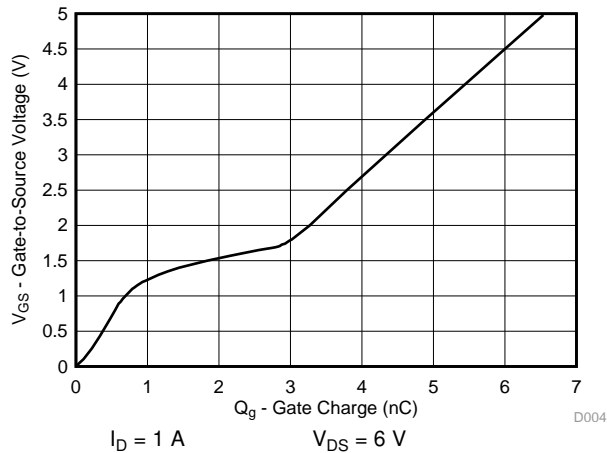


Figure 4. Gate Charge

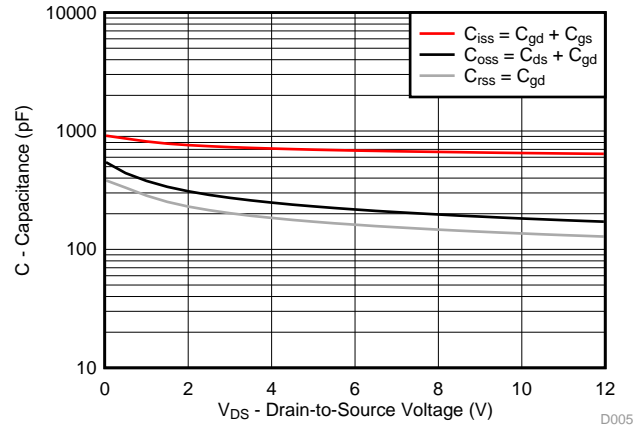


Figure 5. Capacitance

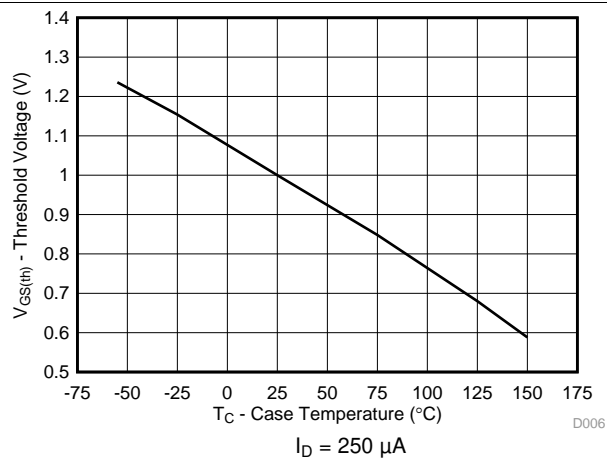


Figure 6. Threshold Voltage vs Temperature

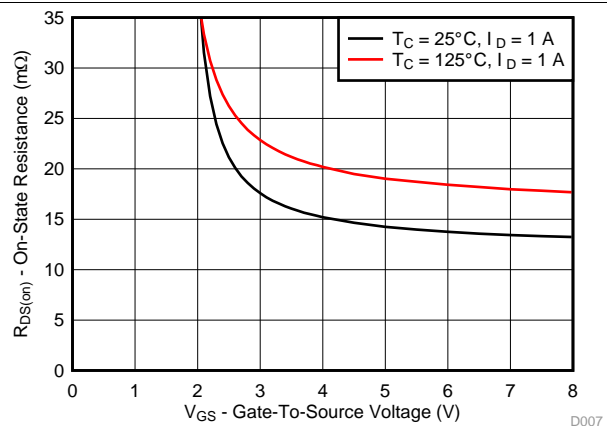
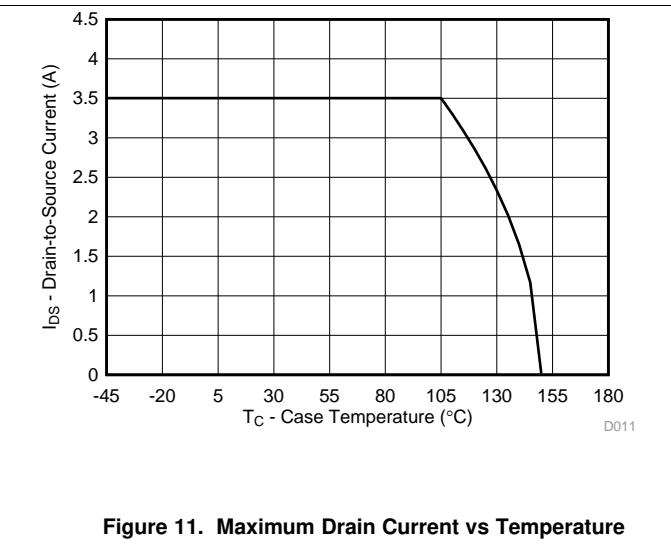
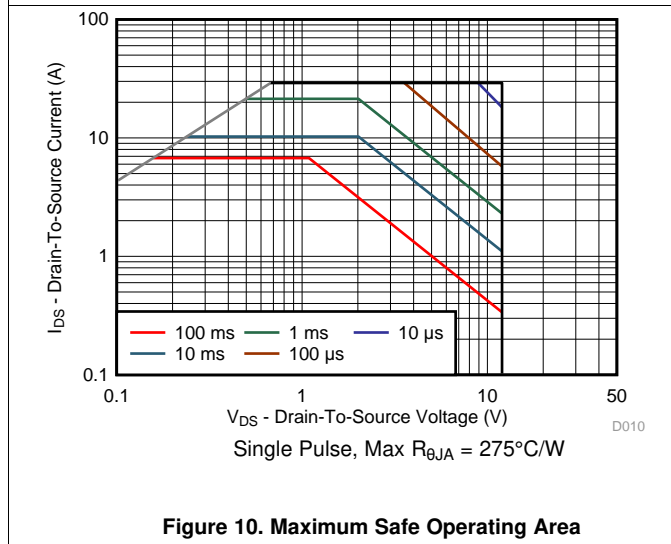
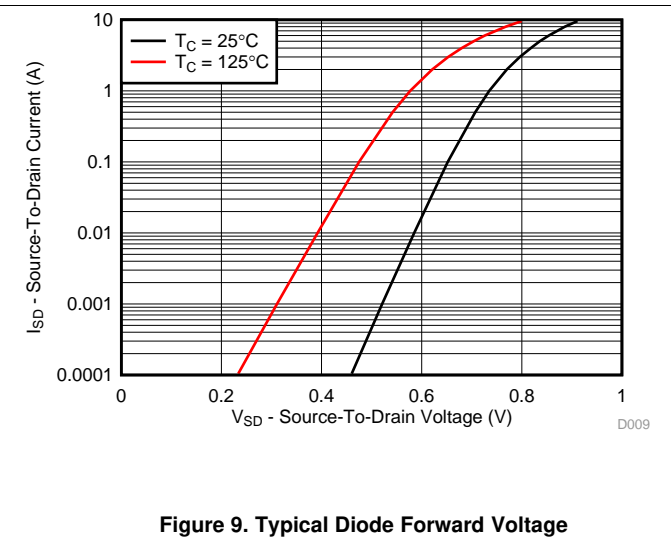
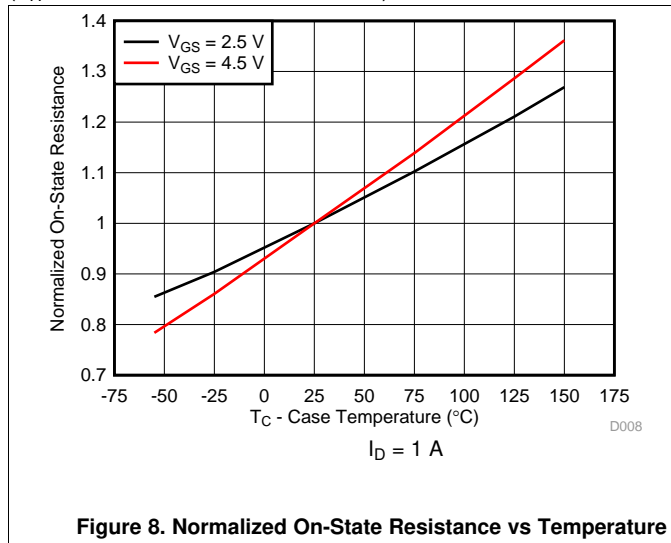


Figure 7. On-State Resistance vs Gate-to-Source Voltage

Typical MOSFET Characteristics (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)



6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

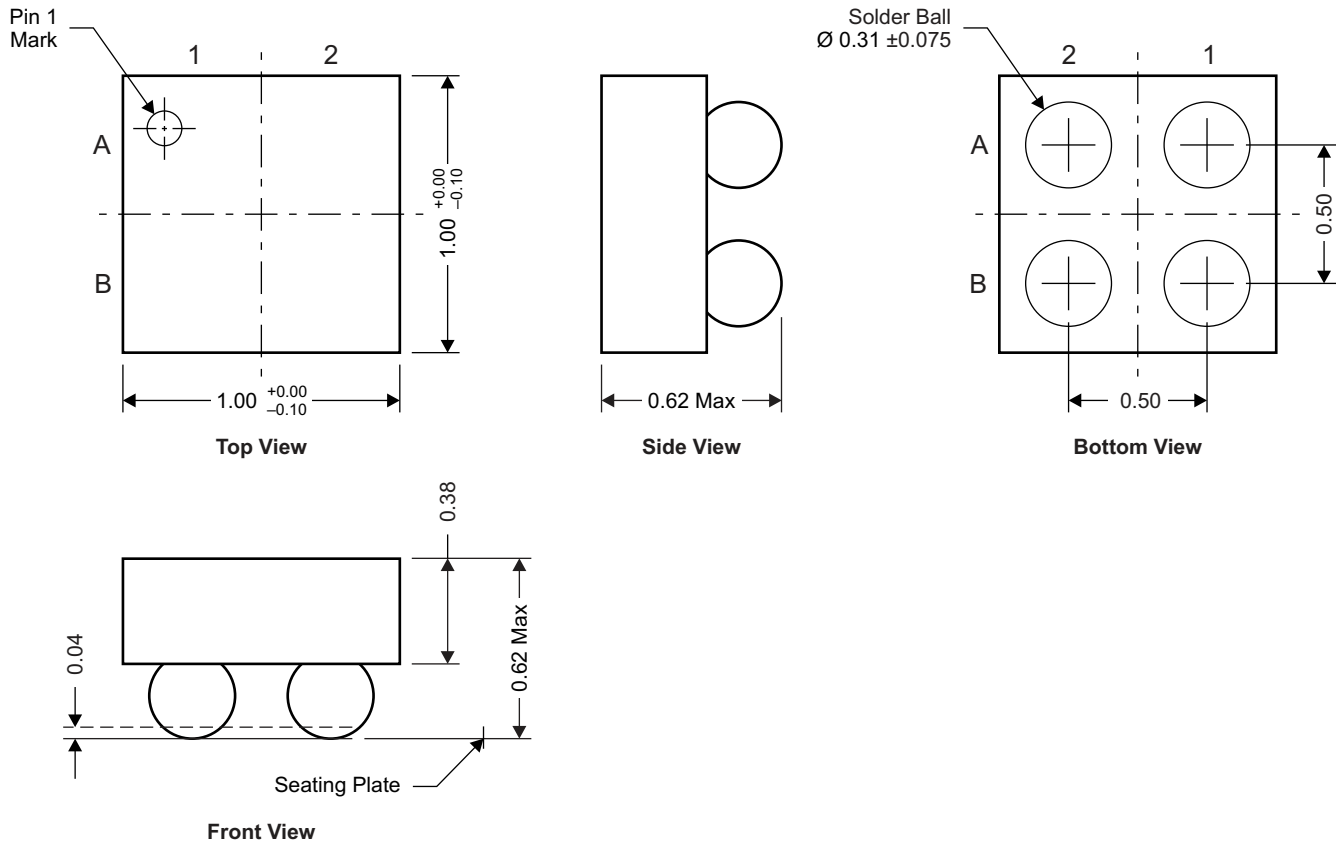
[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 CSD13302W Package Dimensions



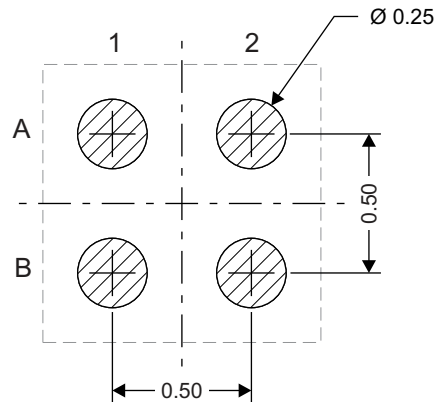
NOTE: All dimensions are in mm (unless otherwise specified)

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Pin Configuration Table

POSITION	DESIGNATION
A2	Source
A1	Gate
B1, B2	Drain

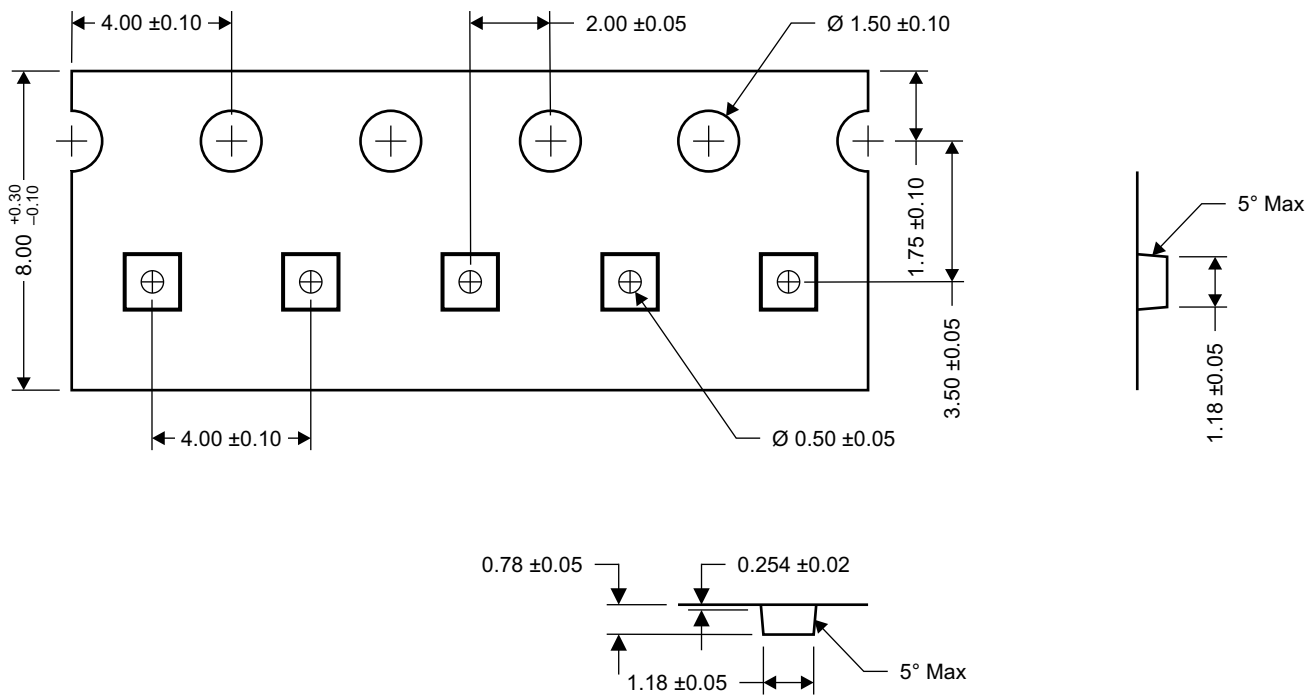
Land Pattern Recommendation



M0152-01

NOTE: All dimensions are in mm (unless otherwise specified)

7.2 Tape and Reel Information



M0153-01

NOTE: All dimensions are in mm (unless otherwise specified)

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD13302W	ACTIVE	DSBGA	YZB	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM		302	Samples
CSD13302WT	ACTIVE	DSBGA	YZB	4	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-55 to 150	302	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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